

N-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

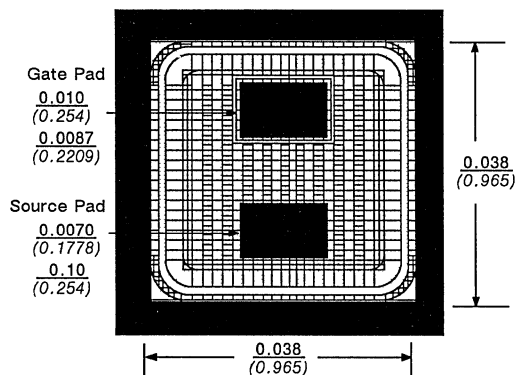
- Switching
- Amplification

FEATURES

- Low $r_{DS(on)} < 4.5 \Omega$

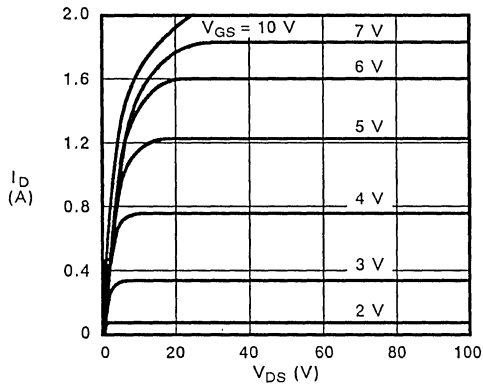
TYPE	PACKAGE	DEVICE
Single	TO-205AD	• VN1206B
	TO-220	• VN1206D
	TO-237	• VN1206M, VN1210M
	TO-92	• VN1206L, VN1210L
	Chip	• Available as above specifications

GEOMETRY DIAGRAM

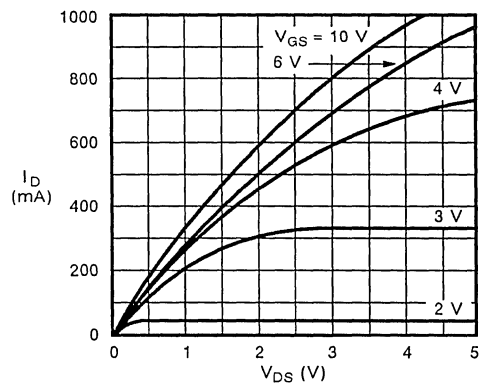


TYPICAL CHARACTERISTICS

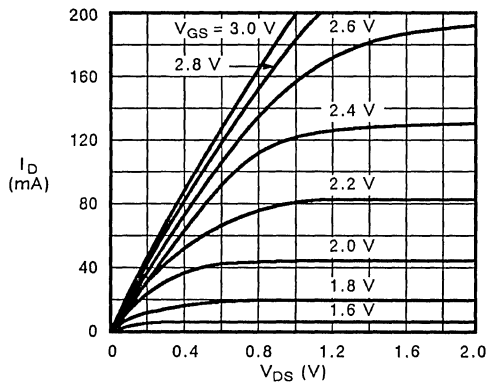
Output Characteristics



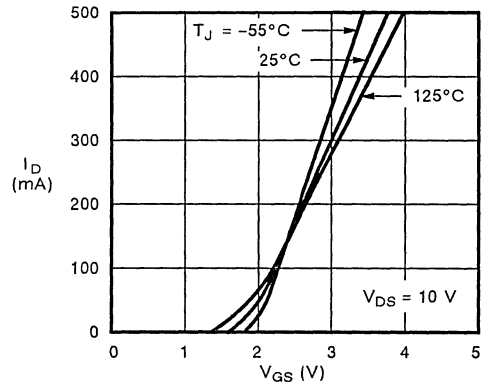
Ohmic Region Characteristics



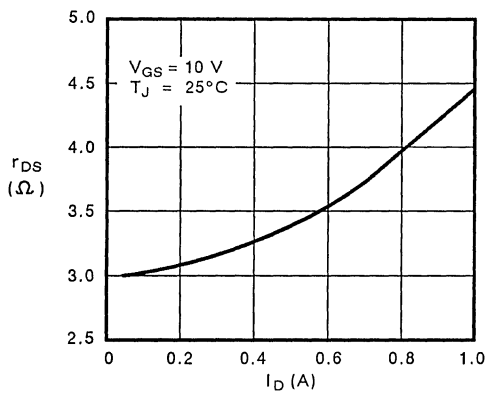
Output Characteristics for Low Gate Drive



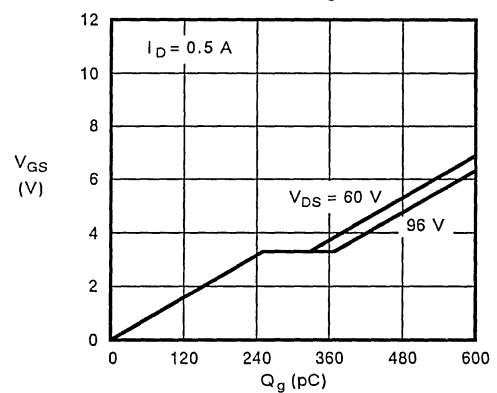
Transfer Characteristics



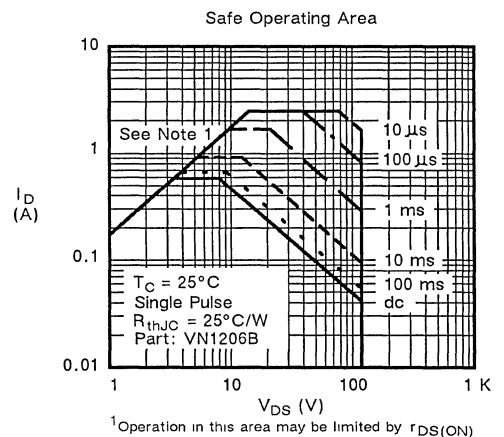
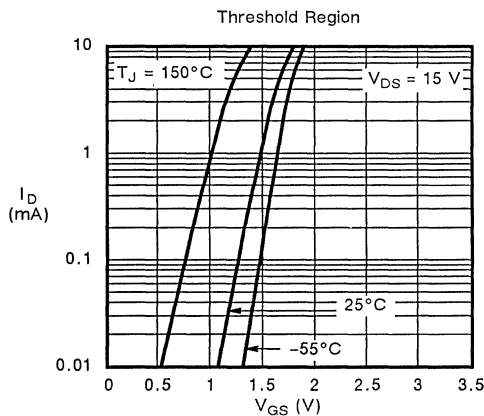
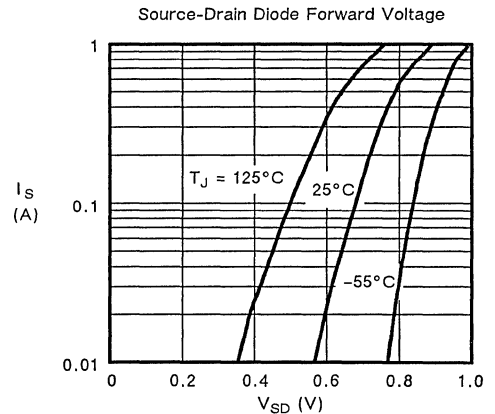
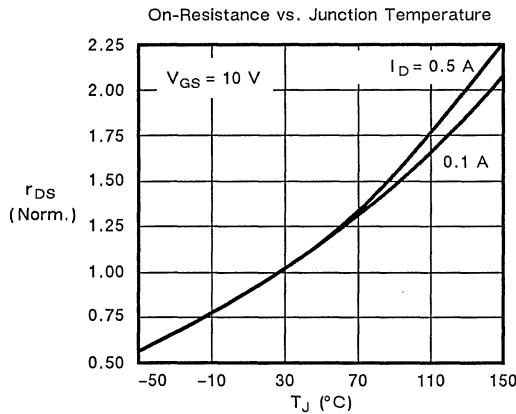
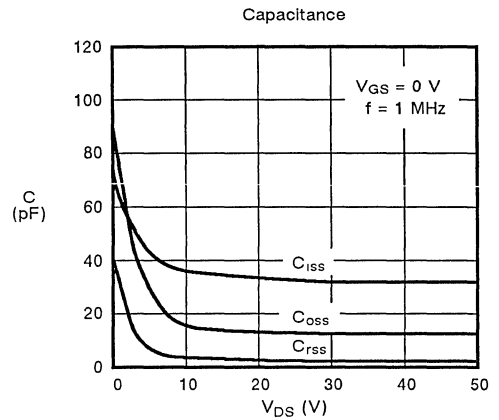
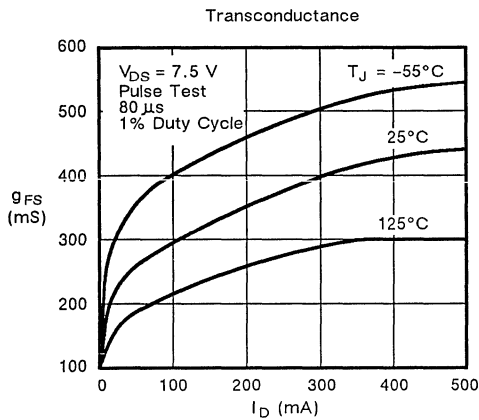
On-Resistance



Gate Charge

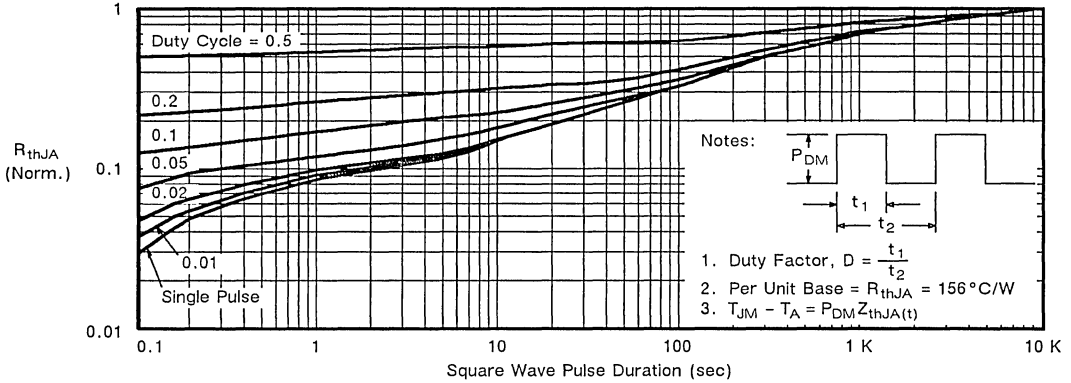


TYPICAL CHARACTERISTICS

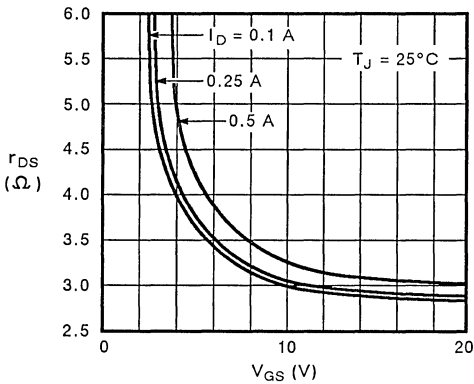


TYPICAL CHARACTERISTICS

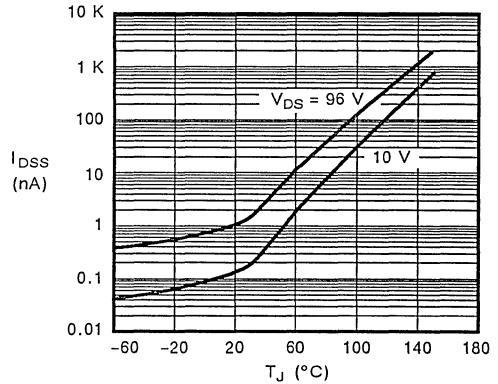
Normalized Effective Transient Thermal Impedance, Junction-to-Ambient (TO-92)



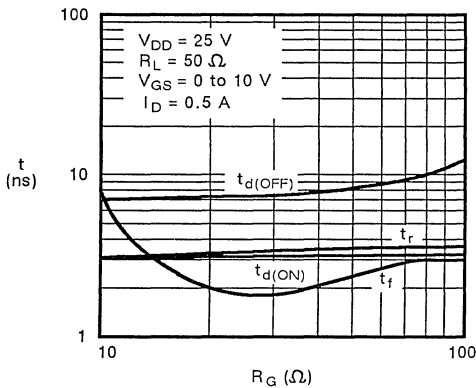
On-Resistance vs. Gate to Source Voltage



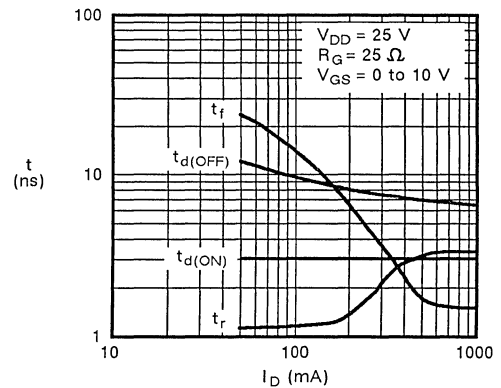
Off State Current



Drive Resistance Effects on Switching



Load Condition Effects on Switching



TYPICAL CHARACTERISTICS

